## Supporting information for

## Design nanoporous metal thin films via solid state interfacial dealloying

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Video S1. 3D XRF nano-tomography of 460C-30 sample

Video S2. 3D STEM-EDX nano-tomography of 460C-30 sample.

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**Figure S1**. SEM cross-section view of  $Ti_{30}Cu_{70}$  at.% films dealloyed by Mg at 460°C for 30 min, with (a) a silicon wafer as the substrate: (left) the pristine Ti-Cu film, and (right) the dealloyed Ti-Cu film, and (b) a borosilicate glass as the substrate: (left) the pristine Ti-Cu film, and (right) the dealloyed Ti-Cu film.



**Figure S2**. Segmented images of Ti EDX mapping of (a) 460C-30 and (b) 460C-30-E with different threshold values ( $I_{th}$ ) and their corresponding ligament size distribution



**Figure S3**. XPS analysis on 460C-30 sample after sputtering by Ar<sup>+</sup> at 1.5 keV at different times.



**Figure S4**. SEM cross-section view of  $Ti_{30}Cu_{70}$  at.% films dealloyed by Mg at 460°C for 30 min, without the Ta barrier layer. A silicon wafer was used as a substrate: (a) the pristine Ti-Cu film, and (b) the dealloyed Ti-Cu film.



Figure S5. Overlap of Ti and Mg EDX maps from the 460C-30 sample.

Systems	Atomic radius of each element	Largest atomic radius ratio in the system	Atomic radius ratio between the soluble and the solvent element (dealloying agent)
(Ta-Ti)-Zr <sup>1</sup>	Ta: 1.430 Ti: 1.462 Zr: 1.603	Ti/Zr = 1.462/1.603 = 0.912	Ti/Zr = 1.462/1.603 = 0.912
(Ta-Ti)-Cu	Ta: 1.430 Ti: 1.462 Cu: 1.278	Cu/Ti = 1.278/1.462 = 0.874	Cu/Ti = 1.278/1.462 = 0.874
(Fe-Ni)-Cu <sup>1</sup>	Fe: 1.241 Ni: 1.246 Cu: 1.278	Cu/Fe = 1.241/1.278 = 0.971	Cu/Ni = 1.246/1.278 = 0.975
(Ti-Cu)-Mg	Ti: 1.462 Cu:1.278 Mg: 1.601	Cu/Mg = 1.278/1.601 = 0.798	Cu/Mg = 1.278/1.601 = 0.798
(Ti-Mo-Cu)-Mg <sup>2</sup>	Ti: 1.462 Cu:1.278 Mo: 1.363 Mg: 1.601	Cu/Mg = 1.278/1.601 = 0.798	Cu/Mg = 1.278/1.601 = 0.798
(Fe-Ni)-Mg <sup>3</sup>	Fe: 1.241 Ni: 1.246 Mg: 1.601	Fe/Mg = 1.241/1.601 = 0.775	Ni/Mg = 1.249/1.601 = 0.780
(Fe-Cr-Ni)-Mg <sup>4</sup>	Fe: 1.241 Ni: 1.246 Cr: 1.249 Mg: 1.601	Fe/Mg = 1.241/1.601 = 0.775	Ni/Mg = 1.249/1.601 = 0.780

Table S1. Summary of atomic radius ratio differences in previously reported SSID systems.

## References

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